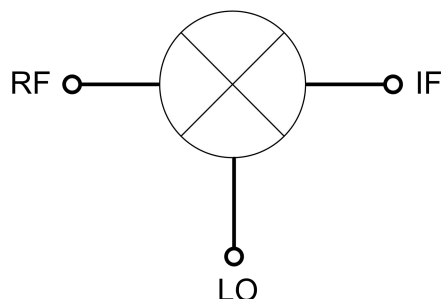


## GaAs MMIC Mixer Chip, 12GHz-46GHz

### Performance characteristics

- RF/LO frequency range: 12 - 46 GHz
- IF frequency range : DC-16GHz
- Conversion loss : 8 dB@+15dBm LO input
- LO-RF isolation: 46dB
- LO-IF isolation : 22dB
- RF-IF isolation : 33 dB
- Local oscillator power: +13dBm~+17dBm
- Chip size: 1.0 x 0.95 x 0.1mm

### Block Diagram



### Product Introduction

GMX-1246A is a GaAs MMIC double balanced mixer, covering 12 GHz~ 46 GHz , IF frequency coverage DC~ 16 GHz , conversion loss 8 dB , LO/RF isolation 46d B , LO/IF isolation 22 dB , RF/IF isolation 33 dB , typical LO input power +15dBm. The chip uses on-chip through-hole metallization technology to ensure good grounding, and no additional grounding measures are required. Easy to use. The back of the chip is metallized, suitable for eutectic sintering or conductive adhesive bonding. There is no DC blocking capacitor at the RF , LO, and IF ports .

### Use restriction parameter <sup>1</sup>

Maximum RF input power	+22dBm
Maximum LO input power	+22dBm
Maximum IF input power	+22dBm
Operating temperature	-55 ~ +85°C
storage temperature	-65 ~ +150°C

【1】 Exceeding any of these maximum limits may cause permanent damage.

### Electrical performance parameters ( $T_A = +25^\circ\text{C}$ , IF = 100MHz , LO = + 15dBm )

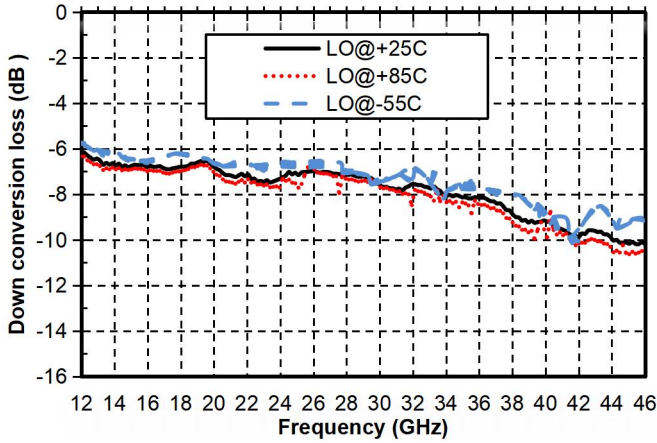
index	Minimum	Typical Value	Maximum	unit
RF frequency range	12-46			GHz
LO frequency range	12-46			GHz
IF frequency	DC-16			GHz
Frequency conversion loss	-	8	-	dB
LO-RF Isolation	-	46	-	dB
LO-IF isolation	-	twenty two	-	dB
RF-IF isolation	-	33	-	dB
RF input P-1dB	11			dB m
IIP3	twenty one			dBm

The above parameters are all tested in down-conversion mode, with intermediate frequency 0.1GHz and local oscillator power + 15dBm.

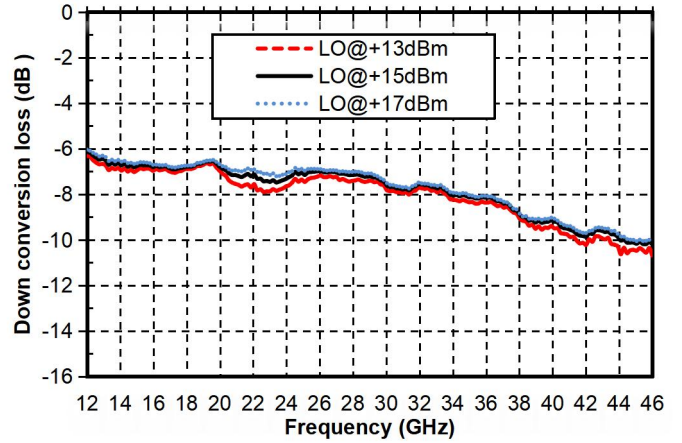
## GaAs MMIC Mixer Chip, 12GHz-46GHz

### Main index test curve

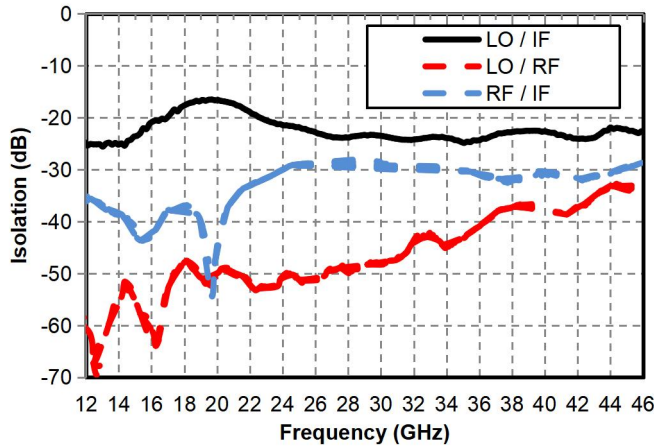
Downconversion loss vs. temperature @ LO = +15dBm



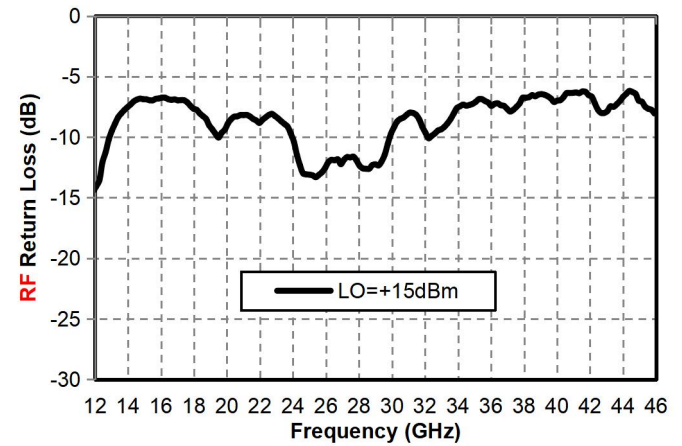
Downconversion Loss vs. LO Power



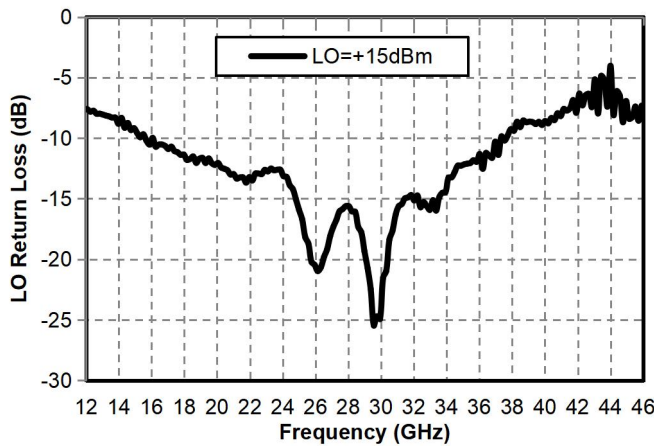
Isolation @ LO = +15dBm



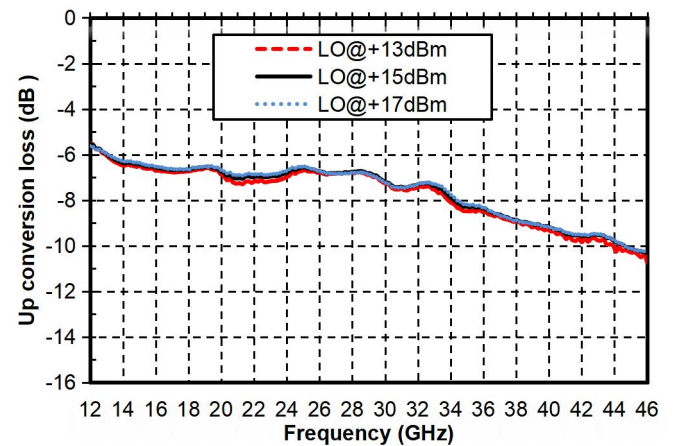
RF Return Loss Vs. Frequency



LO Return Loss Vs. Frequency

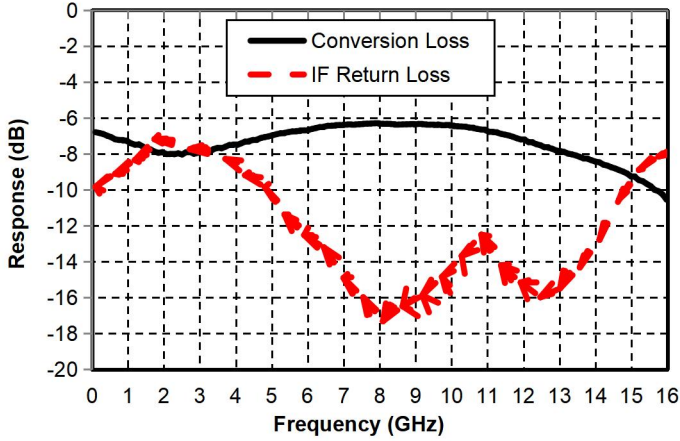


Upconversion Loss vs. LO Power

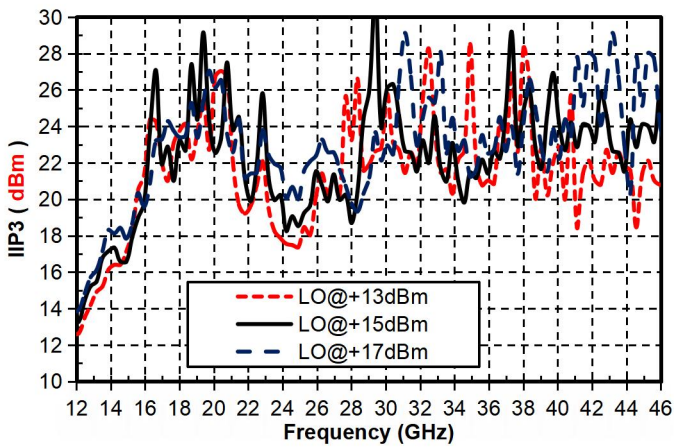


## GaAs MMIC Mixer Chip, 12GHz-46GHz

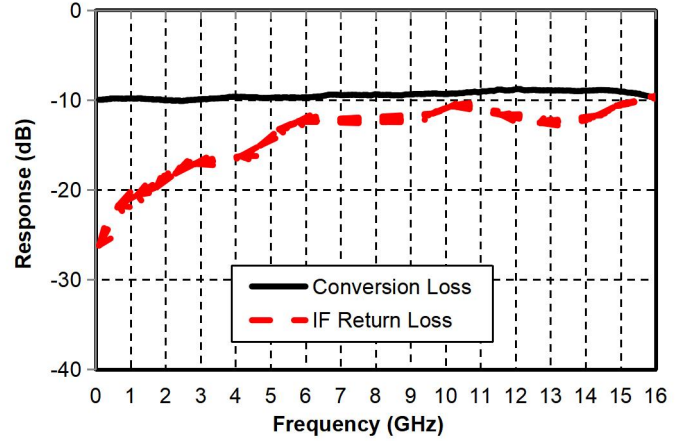
Down-conversion IF bandwidth, return loss  
@LO=14G, 15dBm



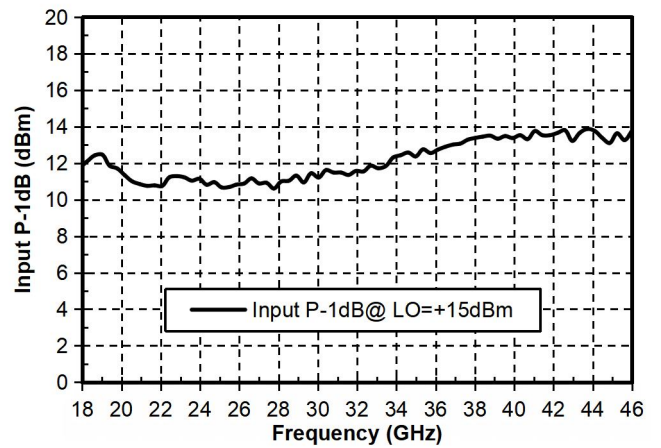
IIP3



Down-conversion IF bandwidth, return loss  
@LO=46G, 15dBm



P-1 vs. Frequency



## GaAs MMIC Mixer Chip, 12GHz-46GHz

### LO harmonic leakage

LO(GHz) 15dBm	nLO (measured at RF port) dBc		
	1	2	3
10	58	29	52
12	56	29	52
14	55	28	50
16	65	27	53
18	46	27	/
20	47	34	/
twenty two	50	45	/
twenty four	50	49	/
26	50	/	/
28	49	/	/
30	47	/	/
32	42	/	/
34	43	/	/
36	40	/	/
38	38	/	/
40	37	/	/
42	35	/	/
44	33	/	/

## GaAs MMIC Mixer Chip, 12GHz-46GHz

### Down-conversion combined spurious suppression

mRF	nLO				
	0	1	2	3	4
0	xxx	-7	29	twenty three	/
1	29	0	36	47	45
2	86	41	58	41	80
3	88	93	81	65	87
4	/	/	/	85	97

Test conditions: RF = 14.1GHz @ -10dBm , LO = 14GHz @ 15dBm , all values are relative values of  $1*RF - 1*LO(P\_IF, dBm)$  , unit is dBc .

mRF	nLO				
	0	1	2	3	4
0	xxx	-10	/	/	/
1	twenty one	0	46	/	/
2	/	61	75	61	/
3	/	/	/	73	/
4	/	/	/	/	102

Test conditions: RF = 27.1GHz@-10dBm , LO = 27GHz @ 15dBm , all values are relative values of  $1*RF-1*LO(P\_IF, dBm)$  , unit is dBc .

### Up-conversion combined spurious suppression

iF	nLO				
	0	1	2	3	4
0	xxx	3	-twenty two	1	-5
1	twenty one	0	20	-11	14
2	26	85	26	40	32
3	50	68	60	39	50
4	68	76	/	68	63

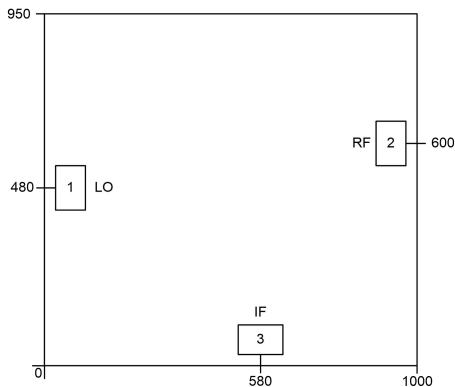
Test conditions: RF = 5.3 GHz @-10 dBm, LO = 12 GHz @ 15 dBm , all values are relative values of  $1 * LO - 1 * IF ( P\_RF , dBm )$  , unit: dBc .

iF	nLO				
	0	1	2	3	4
0	xxx	13	-9	/	/
1	twenty four	0	20	15	/
2	45	106	45	49	/
3	64	67	63	54	71
4	83	85	/	89	87

Test conditions: RF = 8.3 GHz @-10dBm, LO = 18 GHz@ 15dBm , all values are relative values of 1\* LO - 1 \* IF ( P\_RF , dBm ), unit: dBc .

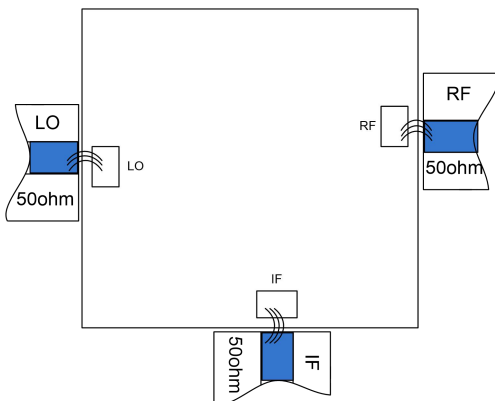
## GaAs MMIC Mixer Chip, 12GHz-46GHz

### Appearance structure <sup>2</sup>



【2】 The units in the figure are all micrometers (dimensional tolerance: ±50um.)

### Recommended assembly drawing



### Bonding point definition

Bonding point number	Function Symbol	Functional Description
1	RF	RF signal end, requires external DC blocking capacitor
2	IF	Intermediate frequency signal end, requires external DC blocking capacitor
3	LO	The local oscillator signal terminal requires an external DC blocking capacitor
Chip bottom	GND	The bottom of the chip needs to be well grounded to RF and DC

Note 1: LO and RF ports can be used interchangeably, but the electrical performance indicators may vary.

Note 2: It is recommended to solder three gold bonding wires to the pad.